

SCHOTTKY RECTIFIER
HIGH EFFICIENCY SERIES

22GQ100
30 Amp, 100V

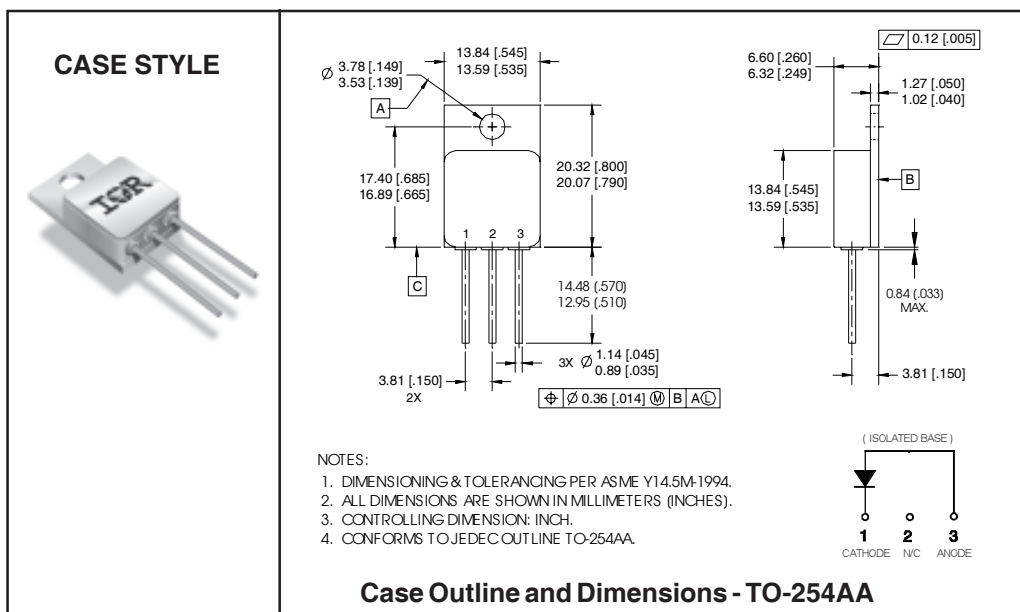
Major Ratings and Characteristics

Characteristics	Limits	Units
$I_{F(AV)}$ Rectangular Waveform	30	A
V_{RRM}	100	V
I_{FSM} @ $t_p = 8.3ms$ half-sine	400	A
V_F @ 20Apk, $T_J = 125^\circ C$	0.73	V
T_J, T_{stg} Operating and storage	-55 to 150	$^\circ C$

Description/Features

The 22GQ100 Schottky rectifier has been expressly designed to meet the rigorous requirements of HiRel environments. It is packaged in the hermetic isolated TO-254AA package. The device's forward voltage drop and reverse leakage current are optimized for the lowest power loss and the highest circuit efficiency for typical high frequency switching power supplies and resonant power converters. Full MIL-PRF-19500 quality conformance testing is available on source controlled drawings to TX, TXV and S levels.

- Hermetically Sealed
- High Frequency Operation
- Guard Ring for Enhanced Ruggedness and Long Term Reliability
- Electrically Isolated
- ESD Rating: Class 3A per MIL-STD-750, Method 1020



22GQ100

International
IOR Rectifier

Voltage Ratings

Parameters	22GQ100
V_R Max. DC Reverse Voltage (V)	100
V_{RWM} Max. Working Peak Reverse Voltage (V)	

Absolute Maximum Ratings

Parameters	Limits	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current See Fig. 5	30	A	50% duty cycle @ $T_C = 113^\circ\text{C}$, rectangular waveform
I_{FSM} Max. Peak One Cycle Non - Repetitive Surge Current	400	A	@ $t_p = 8.3$ ms half-sine

Electrical Specifications

Parameters	Limits	Units	Conditions
V_{FM} Max. Forward Voltage Drop See Fig. 1 ①	0.86	V	@ 20A $T_J = -55^\circ\text{C}$
	0.99	V	@ 35A $T_J = -55^\circ\text{C}$
	0.84	V	@ 20A $T_J = 25^\circ\text{C}$
	0.98	V	@ 35A $T_J = 25^\circ\text{C}$
	0.73	V	@ 20A $T_J = 125^\circ\text{C}$
I_{RM} Max. Reverse Leakage Current See Fig. 2 ①	0.8	mA	$T_J = 25^\circ\text{C}$ $V_R = \text{rated } V_R$
	45	mA	$T_J = 125^\circ\text{C}$ $V_R = \text{rated } V_R$
C_T Max. Junction Capacitance	1400	pF	$V_R = 5V_{DC}$ (1MHz, 25°C)
L_S Typical Series Inductance	7.8	nH	Measured from anode lead to cathode lead 6mm (0.025 in.) from package

Thermal-Mechanical Specifications

Parameters	Limits	Units	Conditions
T_J Max. Junction Temperature Range	-55 to 150	$^\circ\text{C}$	
T_{stg} Max. Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
R_{thJC} Max. Thermal Resistance, Junction to Case	1.0	$^\circ\text{C}/\text{W}$	DC operation See Fig. 4
wt Weight (Typical)	9.3	g	
Die Size	200X200	mils	
Case Style	TO-254AA		

① Pulse Width < 300 μs , Duty Cycle < 2%

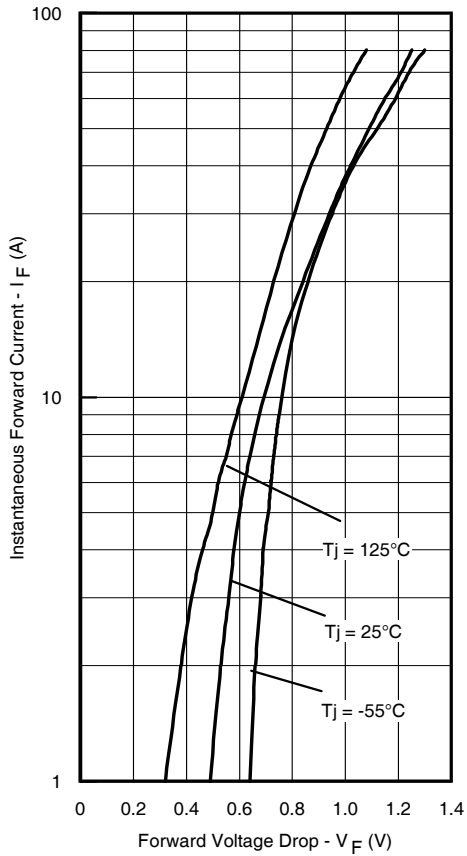


Fig. 1 - Maximum Forward Voltage Drop Characteristics

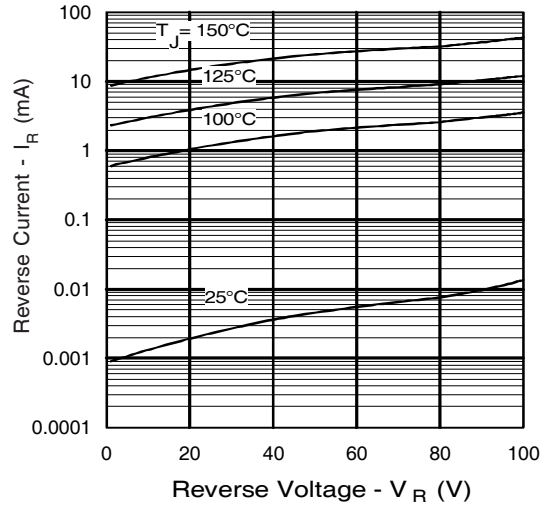


Fig. 2 - Typical Values of Reverse Current Vs. Reverse Voltage

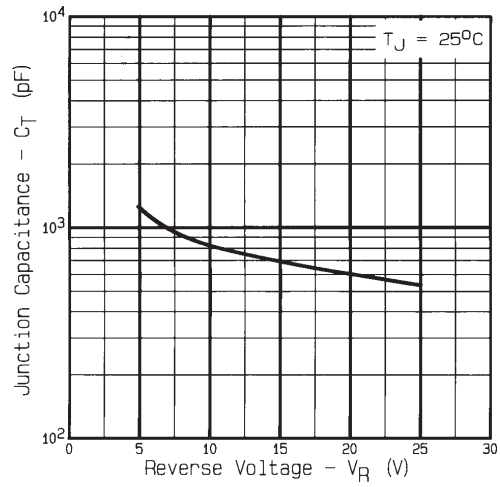


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

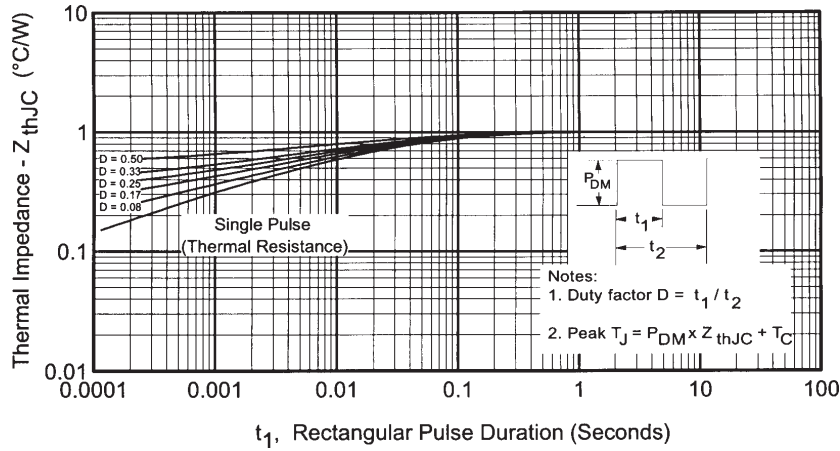


Fig. 4 - Max. Thermal Impedance Z_{thJC} Characteristics

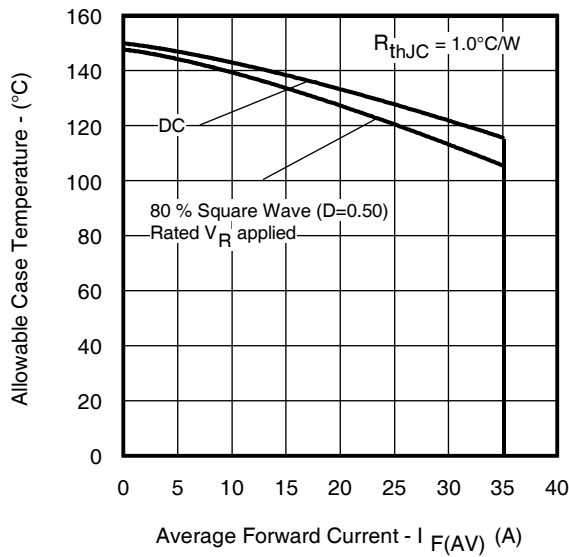


Fig. 5 - Max. Allowable Case Temperature Vs. Average Forward Current